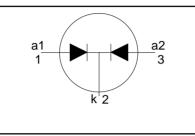
#### **Rectifier diodes** ultrafast, rugged

### **BYQ40EW** series

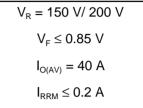
#### **FEATURES**

- Low forward volt drop
- · Fast switching
- Soft recovery characteristic
- Reverse surge capability
- High thermal cycling performance
  Low thermal resistance

#### SYMBOL



### QUICK REFERENCE DATA



## $t_{rr} \leq 30 \text{ ns}$

#### **GENERAL DESCRIPTION**

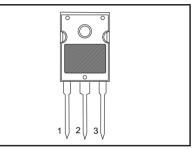
Dual, common cathode, ultra-fast, epitaxial rectifier diodes intended for use as output rectifiers in high frequency switched mode power supplies.

The BYQ40EW series is supplied in the conventional leaded SOT429 (TO247) package.

#### PINNING

PIN	DESCRIPTION
1	anode 1
2	cathode
3	anode 2
tab	cathode

### SOT429 (TO247)



#### **LIMITING VALUES**

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	N. MAX.		UNIT
V <sub>rrm</sub> V <sub>rwm</sub> V <sub>r</sub>	Peak repetitive reverse voltage Crest working reverse voltage Continuous reverse voltage	BYQ40EW	- - -	<b>-150</b> 150 150 150	<b>-200</b> 200 200 200	V V V
I <sub>O(AV)</sub>	Average rectified output current (both diodes conducting)	square wave δ = 0.5; T <sub>mb</sub> ≤ 110 °C	-	4	0	A
I <sub>FRM</sub>	Repetitive peak forward current per diode	t = 25 μs; δ = 0.5; T <sub>mb</sub> ≤ 110 °C	-	4	0	A
I <sub>FSM</sub>	Non-repetitive peak forward current per diode	t = 10 ms t = 8.3 ms sinusoidal; with reapplied V <sub>RWM(max)</sub>	-		00 25	A A
I <sub>RRM</sub>	Repetitive peak reverse current per diode	$t_p = 2 \ \mu s; \ \delta = 0.001$	-	0	.2	A
I <sub>RSM</sub>	Non-repetitive peak reverse current per diode	t <sub>p</sub> = 100 μs	-	0	.2	A
T <sub>stg</sub> T <sub>j</sub>	Storage temperature Operating junction temperature		-40 -		50 50	Ĵ Ĵ

#### **ESD LIMITING VALUE**

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>c</sub>	5	Human body model; C = 250 pF; R = 1.5 k $\Omega$	-	8	kV

# Rectifier diodes ultrafast, rugged

### **BYQ40EW** series

#### THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
R <sub>th j-mb</sub> R <sub>th j-a</sub>	mounting base	per diode both diodes conducting in free air		- - 45	1.05 0.75 -	K/W K/W K/W

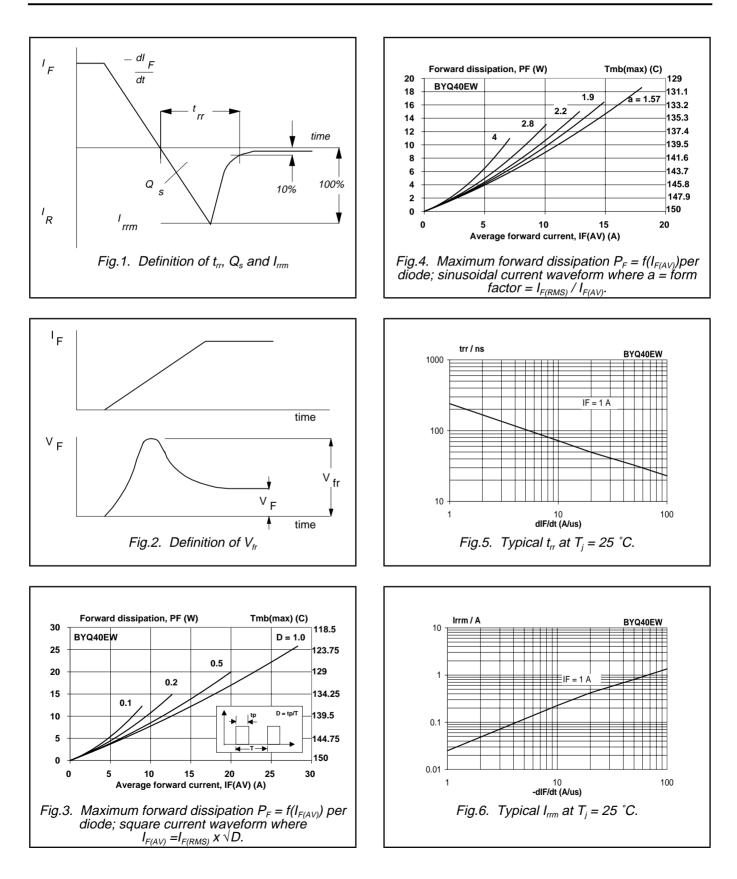
#### **ELECTRICAL CHARACTERISTICS**

characteristics are per diode at  $T_i = 25$  °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V <sub>F</sub>	Forward voltage	I <sub>F</sub> = 20 A; T <sub>i</sub> = 150°C	-	0.8	0.85	V
	-	$I_{\rm F} = 20  {\rm A}^{-1}$	-	0.97	1.05	V
		$I_{F} = 40 \text{ A}$	-	1.06	1.20	V
I <sub>R</sub>	Reverse current	$\dot{V}_{R} = V_{RWM}$	-	6	100	μA
		$V_{R}^{r} = V_{RWM}^{r}; T_{j} = 100 \text{ °C}$ I <sub>F</sub> = 2 A; V <sub>R</sub> ≥ 30 V; -dI <sub>F</sub> /dt = 20 A/µs	-	0.7	1	mΑ
Q <sub>s</sub>	Reverse recovery charge	$I_{\rm F} = 2 \text{ A}; V_{\rm R} \ge 30 \text{ V}; -dI_{\rm F}/dt = 20 \text{ A}/\mu \text{s}$	-	8	18	nC
t <sub>rr</sub>	Reverse recovery time	$I_{\rm F} = 1 \text{ A}; V_{\rm R} \ge 30 \text{ V};$	-	23	30	ns
		-dl <sub>F</sub> /dt = 100 A/μs				
V <sub>fr</sub>	Forward recovery voltage	$I_{F} = 1 \text{ A}; \text{ d}I_{F}/\text{d}t = 10 \text{ A}/\mu\text{s}$	-	0.7	-	V

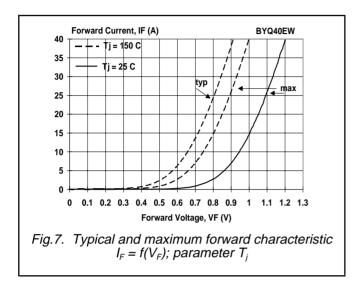
# Rectifier diodes ultrafast, rugged

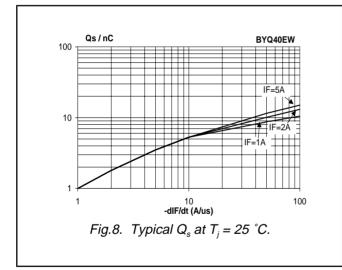
## **BYQ40EW** series

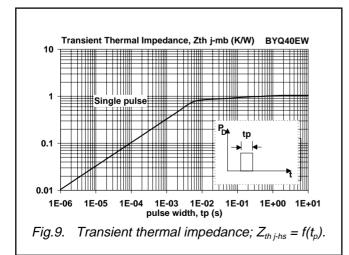


**BYQ40EW** series

# Rectifier diodes ultrafast, rugged



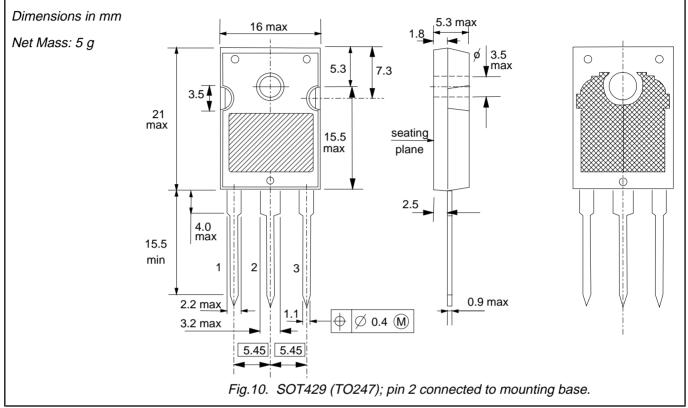




#### **Rectifier diodes** ultrafast, rugged

### **BYQ40EW** series

#### **MECHANICAL DATA**



#### Notes

Refer to mounting instructions for SOT429 envelope.
 Epoxy meets UL94 V0 at 1/8".

# Rectifier diodes ultrafast, rugged

#### **BYQ40EW** series

#### DEFINITIONS

Data sheet status					
Objective specification This data sheet contains target or goal specifications for product development.					
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.				
Product specification	This data sheet contains final product specifications.				
Limiting values					
or more of the limiting val operation of the device at	Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.				
Application information					
Where application information	Where application information is given, it is advisory and does not form part of the specification.				
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